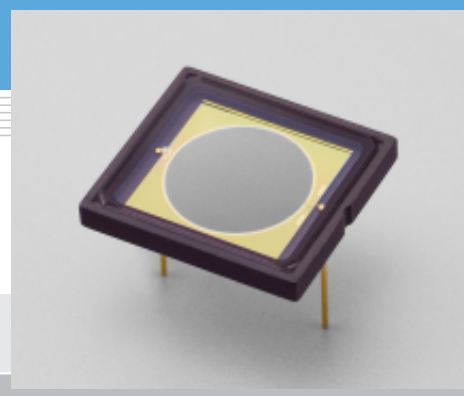


NEW

PHOTODIODE



InGaAs PIN photodiode

G8370-10

Ceramic package with large active area ($\phi 10$ mm)

Features

- Large active area: $\phi 10$ mm
- High sensitivity: 0.95 A/W Typ. ($\lambda=1.55$ μm)
- Low dark current
- Low PDL: 5 mdB Typ., 10 mdB Max.
- Photo response non-uniformity: ± 2 % Typ.

Applications

- LD power monitor
- LD aging equipment

■ General / Absolute maximum ratings

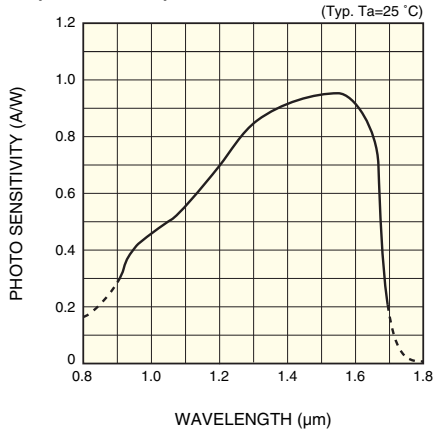
| Parameter | Symbol | Value | Unit |
|-----------------------|------------|--------------|--------------------|
| Active area | - | $\phi 10$ | mm |
| Reverse voltage | V_R Max. | 1 | V |
| Operating temperature | $T_{opr.}$ | -25 to +70 * | $^{\circ}\text{C}$ |
| Storage temperature | $T_{stg.}$ | -25 to +70 * | $^{\circ}\text{C}$ |

* No condensation

■ Electrical and optical characteristics ($T_a=25$ $^{\circ}\text{C}$)

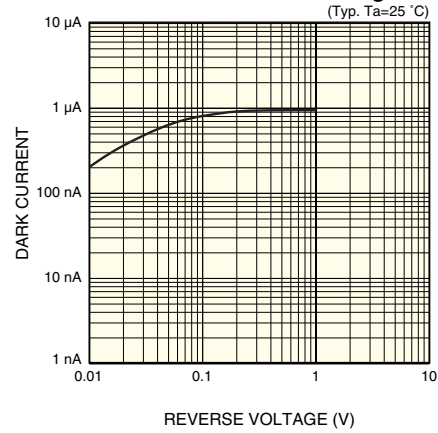
| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------|-------------|---|------|----------------------|------|--|
| Spectral response range | λ | | - | 0.9 to 1.7 | - | μm |
| Peak sensitivity wavelength | λ_p | | - | 1.55 | - | μm |
| Photo sensitivity | S | $\lambda=1.3$ μm | 0.8 | 0.85 | - | A/W |
| | | $\lambda=\lambda_p$ | 0.85 | 0.95 | - | A/W |
| Dark current | I_D | $V_R=10$ mV | - | 0.2 | 2 | μA |
| Shunt resistance | Rsh | $V_R=10$ mV | 5 | 50 | - | $\text{k}\Omega$ |
| Terminal capacitance | C_t | $V_R=0$ V, $f=1$ MHz | - | 20 | - | nF |
| Cut-off frequency | f_c | $V_R=0$ V, $R_L=50$ Ω | - | 100 | - | kHz |
| Noise equivalent power | NEP | $\lambda=\lambda_p$ | - | 6×10^{-13} | - | $\text{W}/\text{Hz}^{1/2}$ |
| Detectivity | D^* | $\lambda=\lambda_p$ | - | 1.5×10^{12} | - | $\text{cm}\cdot\text{Hz}^{1/2}/\text{W}$ |
| Photo response non-uniformity | PRNU | 80 % of active area | - | ± 2 | - | % |
| PDL | - | $V_R=0$ V, $\lambda=1.55$ μm | - | 5 | 10 | mdB |

■ Spectral response



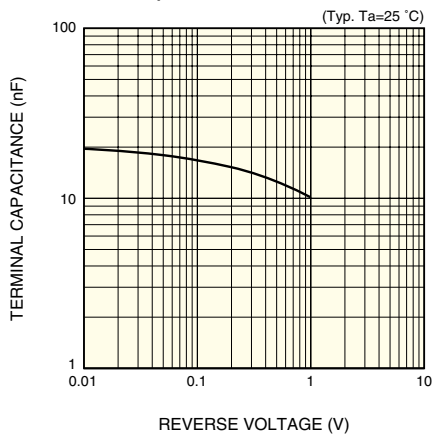
KIRDB0284EA

■ Dark current vs. reverse voltage



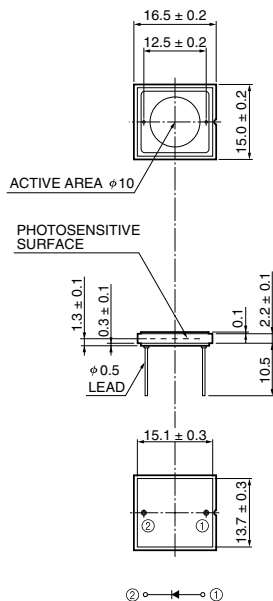
KIRDB0285EA

■ Terminal capacitance vs. reverse voltage



KIRDB0286EA

■ Dimensional outline (unit: mm)



KIRDA0167EA

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